## MSKSEMI



## Features

- 350W peak pulse power $(8 / 20 \mu s)$
- Ultra low capacitance : 1.0pF typical
- Ultra low leakage: nA level
- Low Operating: $3.3 \mathrm{~V}, 5 \mathrm{~V}, 8 \mathrm{~V}, 12 \mathrm{~V}, 15 \mathrm{~V}, 24 \mathrm{~V}$
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
- IEC 61000-4-2 (ESD) immunity test

Air discharge: $\pm 30 \mathrm{kV}$
Contact discharge: $\pm 30 \mathrm{kV}$

- IEC61000-4-4 (EFT) 40A (5/50ns)
- RoHS Compliant


## Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 perJ-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below


Circuit and Pin Schematic

SOD-323

## Applications

- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{A}}=\mathbf{2 5 ^ { \circ }} \mathrm{C}$ unless otherwise specified)

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| ESD per IEC 61000-4-2 (Air) | VESD | $\pm 30$ | $\pm 30$ |
| ESD per IEC 61000-4-2 (Contact) | TJ | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| Operating Temperature Range | Tstg | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range |  |  |  |

Electrical Characteristics ( $\mathrm{T}_{\mathbf{A}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| BV03C-MS |  |  |  |  |  |  |
| :--- | :---: | :---: | :---: | :---: | :---: | :--- |
| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
| Reverse Working Voltage | VRWM |  |  | 3.3 | V |  |
| Breakdown Voltage | VBR | 4 |  |  | V | $\mathrm{IT}=1 \mathrm{~mA}$ |
| Reverse Leakage Current | $\mathrm{I}_{\mathrm{R}}$ |  | 1 | 100 | nA | $\mathrm{VRWM}=3.3 \mathrm{~V}$ |
| Clamping Voltage | Vc |  |  | 7 | V | $\mathrm{IPP}=1 \mathrm{~A}(8 \times 20 \mu \mathrm{~s}$ pulse $)$ |
| Clamping Voltage | Vc |  |  | 16 | V | $\mathrm{IPP}=20 \mathrm{~A}(8 \times 20 \mu \mathrm{~s}$ pulse $)$ |
| Peak Pulse Current | IPP |  |  | 20 | A | $\mathrm{tp}=8 / 20 \mu \mathrm{~s}$ |
| Junction Capacitance | CJ |  | 1 |  | pF | $\mathrm{VR}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |

## BV05C-MS

| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
| :--- | :---: | :---: | :---: | :---: | :---: | :--- |
| Reverse Working Voltage | VRWM |  |  | 5 | V |  |
| Breakdown Voltage | VBR | 6 |  |  | V | $\mathrm{IT}=1 \mathrm{~mA}$ |
| Reverse Leakage Current | IR |  | 1 | 100 | nA | VRWM $=5 \mathrm{~V}$ |
| Clamping Voltage | Vc |  |  | 10 | V | $\mathrm{IPP}=1 \mathrm{~A}(8 \times 20 \mu \mathrm{~s}$ pulse $)$ |
| Clamping Voltage | Vc |  |  | 18 | V | $\mathrm{IPP}=18 \mathrm{~A}(8 \times 20 \mu \mathrm{~s}$ pulse $)$ |
| Peak Pulse Current | IPP |  |  | 18 | A | $\mathrm{tp}=8 / 20 \mu \mathrm{~s}$ |
| Junction Capacitance | CJ |  | 1 |  | pF | $\mathrm{VR}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |

BVXXC-MS

## BV08C-MS

| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
| :--- | :---: | :---: | :---: | :---: | :--- | :--- |
| Reverse Working Voltage | VRWM |  |  | 8 | V |  |
| Breakdown Voltage | VBR | 8.5 |  |  | V | $\mathrm{IT}=1 \mathrm{~mA}$ |
| Reverse Leakage Current | IR |  | 1 | 100 | nA | $\mathrm{VRWM}=8 \mathrm{~V}$ |
| Clamping Voltage | VC |  |  | 14 | V | $\mathrm{IPP}=1 \mathrm{~A}(8 \times 20 \mu \mathrm{~s} \mathrm{pulse})$ |
| Clamping Voltage | VC |  |  | 19 | V | $\mathrm{IPP}=13 \mathrm{~A}(8 \times 20 \mu \mathrm{~s} \mathrm{pulse})$ |
| Peak Pulse Current | IPP |  |  | 13 | A | $\mathrm{tp}=8 / 20 \mu \mathrm{~s}$ |
| Junction Capacitance | CJ |  | 1 |  | pF | $\mathrm{VR}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |


| BV12C-MS |  |  |  |  |  |  |
| :--- | :---: | :---: | :---: | :---: | :---: | :--- |
| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
| Reverse Working Voltage | VRWM |  |  | 12 | V |  |
| Breakdown Voltage | VBR | 13.3 |  |  | V | $\mathrm{IT}=1 \mathrm{~mA}$ |
| Reverse Leakage Current | $\mathrm{IR}_{\mathrm{R}}$ |  | 1 | 100 | nA | $\mathrm{VRWM}=12 \mathrm{~V}$ |
| Clamping Voltage | Vc |  |  | 19 | V | $\mathrm{IPP}=1 \mathrm{~A}(8 \times 20 \mu \mathrm{~s}$ pulse $)$ |
| Clamping Voltage | VC |  |  | 25 | V | $\mathrm{IPP}=10 \mathrm{~A}(8 \times 20 \mu \mathrm{~s}$ pulse $)$ |
| Peak Pulse Current | IPP |  |  | 10 | A | $\mathrm{tp}=8 / 20 \mu \mathrm{~s}$ |
| Junction Capacitance | CJ |  | 1 |  | pF | $\mathrm{VR}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |

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## BV15C-MS

| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
| :--- | :---: | :---: | :---: | :---: | :---: | :--- |
| Reverse Working Voltage | VRWM |  |  | 15 | V |  |
| Breakdown Voltage | VBR | 16.7 |  |  | V | $\mathrm{IT}=1 \mathrm{~mA}$ |
| Reverse Leakage Current | IR |  | 1 | 100 | nA | $\mathrm{VRWM}=15 \mathrm{~V}$ |
| Clamping Voltage | VC |  |  | 20 | V | $\mathrm{IPP}=1 \mathrm{~A}(8 \times 20 \mu \mathrm{~s}$ pulse $)$ |
| Clamping Voltage | VC |  |  | 31 | V | $\mathrm{IPP}=8 \mathrm{~A}(8 \times 20 \mu \mathrm{~s} \mathrm{pulse})$ |
| Peak Pulse Current | IPP |  |  | 8 | A | $\mathrm{tp}=8 / 20 \mu \mathrm{~s}$ |
| Junction Capacitance | CJ |  | 1 |  | pF | $\mathrm{VR}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |

## BV24C-MS

| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
| :--- | :---: | :---: | :---: | :---: | :---: | :--- |
| Reverse Working Voltage | VRWM |  |  | 24 | V |  |
| Breakdown Voltage | VBR | 26.7 |  |  | V | $\mathrm{IT}=1 \mathrm{~mA}$ |
| Reverse Leakage Current | I |  | 1 | 100 | nA | $\mathrm{VRWM}=24 \mathrm{~V}$ |
| Clamping Voltage | VC |  |  | 40 | V | $\mathrm{IPP}=1 \mathrm{~A}(8 \times 20 \mu \mathrm{~s}$ pulse $)$ |
| Clamping Voltage | VC |  |  | 71 | V | $\mathrm{IPP}=3.5 \mathrm{~A}(8 \times 20 \mu \mathrm{~s} \mathrm{pulse})$ |
| Peak Pulse Current | IPP |  |  | 3.5 | A | $\mathrm{tp}=8 / 20 \mu \mathrm{~s}$ |
| Junction Capacitance | CJ |  | 1 |  | pF | $\mathrm{VR}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |

## PACKAGE MECHANICAL DATA



| Symbol | Dimensions In Millimeters |  | Dimensions In Inches |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Max. | Min. | Max. |  |  |  |
| A | 0.000 | 1.000 |  | 0.039 |  |  |  |
| A1 | 0.800 | 0.100 | 0.000 | 0.004 |  |  |  |
| A2 | 0.250 | 0.350 | 0.031 | 0.035 |  |  |  |
| b | 0.080 | 0.150 | 0.010 | 0.014 |  |  |  |
| c | 1.200 | 1.400 | 0.003 | 0.006 |  |  |  |
| D | 1.600 | 1.800 | 0.047 | 0.055 |  |  |  |
| E | 2.550 | 2.750 | 0.063 | 0.071 |  |  |  |
| E1 | 0.475 REF. |  | 0.100 | 0.108 |  |  |  |
| L | 0.250 | 0.400 | 0.019 REF. |  |  |  |  |
| L1 | $0^{\circ}$ | $8^{\circ}$ | 0.010 | 0.016 |  |  |  |
| $\theta$ |  |  |  |  |  | $0^{\circ}$ | $8^{\circ}$ |

## Suggested Pad Layout



## Note:

1.Controlling dimension:in millimeters.
2. General tolerance: $\pm 0.05 \mathrm{~mm}$.
3.The pad layout is for reference purposes only.

## REEL SPECIFICATION

| P/N | PKG | QTY |
| :---: | :---: | :---: |
| BVXXC-MS | SOD-323 | 3000 |

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